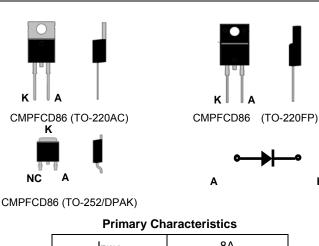


FEATURES

- Fast switching for high efficiency
- Low noise
- Trr ~ 25ns
- Ultra low reverse leakage current
- High voltage ultra faster diode PFC application
- High inrush current

MECHANICAL DATA

- Case : Molded plastic TO-220AC / TO-220FP
- Epoxy : UL94V-0 rate flame retardant
 Terminals : Solder able per MIL-STD-202 method 208
- ♦ 265°C Max. for 10 Seconds
- Maximum Mounting Torque 6 (5) Kg-cm(lbf-in)



CMPFCD86

κ

PFC Diode (8A/600V)

I _{F(AV)}	8A	
V _{RRM}	600 V	
V _{F(typ)}	1.5 V	
I _{R(typ)}	10 µA	
Tj	175 ℃	

ORDERING INFORMATION

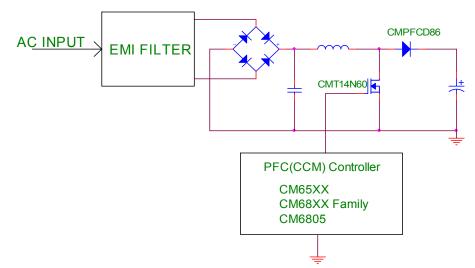
Part Number	Temperature Range	Package
CMPFCD86XN220*	-55℃ to 175℃	TO-220AC
CMPFCD86GN220*	-55℃ to 175℃	TO-220AC
CMPFCD86XN220FP*	-55℃ to 175℃	TO-220FP
CMPFCD86GN220FP*	-55℃ to 175℃	TO-220FP
CMPFCD86XN252*	-55℃ to 175℃	TO-252

*Note : G : Suffix for Pb Free Product

X : Suffix for Halogen Free

*Note : N : TO

APPLICATION CIRCUIT





MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 $^\circ\!C$ ambient temperature unless otherwise specified. Single phase, half wave , 60Hz , resistive or inductive load. For capacitive load , derate current by 20%

Symbol	ymbol Characteristics		CMPFCD86	Unit		
Symbol			Rating	Onit		
V _{RRM}	Recurrent Peak Reverse Voltage			600	V	
V _{DC}	DC Blocking Voltage			600	V	
IF _(AV)	Average Forward Rectified Curr	ent @Tc=140℃		8	А	
	Peak Forward Surge Current					
I _{FSM}	8.3ms single half sine-wave			90	А	
	Super imposed on rated load (J	EDEC Method)				
Irou	Peak Forward Surge Current			110	А	
I _{FSM}	4ms single half sine-wave			110	~	
I _{FSM}	Peak Forward Surge Current 1ms single half sine-wave			200	Α	
'FSM				200		
I _{FSM}	Peak Forward Surge Current 4ms single			90	А	
'F 31VI	Square-wave superimposed on rated load					
I _{FSM}	Peak Forward Surge Current 1.0	•		150	А	
	Square-wave superimposed on rated load (JEDEC Method)					
l ² t	I ² t Value For Fusing Tp=10ms			91	A ² s	
.,		T J=25 ℃		1.5		
V_{F}	Instantaneous Forward Voltage	(Typical) @8A	T J=125 ℃	1.25	V	
	DC Reverse Current		T J=25 ℃	10		
I _R	At Rated DC Blocking Voltage		T 」=150 ℃	45	uA	
	Maximum Reverse Recovery Ti	me				
Trr	Test Conditions : I _F =0.5A , Ir=1.			25		
	Test Conditions : I _F =1A, dI _F /dt =	-50A/uS, V _R =30	DV V	35	nS	
CJ	Typical Junction Capacitance	(note1)		36	pF	
-			TO-220AC			
R _{0JC} Typical Thermal Resistance	(note2)	TO-252	2.2	°C/W		
		TO-220FP	4.6			
TJ	Operating Temperature Range			-55~+175	°C	
T _{STG}	Storage Temperature Range	age Temperature Range		-55~+175	°C	
R _{0JA} Typical Thermal Resistance		TO-220AC		60		
	Typical Thermal Resistance	TO-220FP		50	°C	
		TO-252		80		

Notes: 1. Measured at 1.0MHz and applied reverse voltage of 4.0 Volts DC.

2. Thermal Resistance junction to case.



TYPICAL CHARACTERISTICS

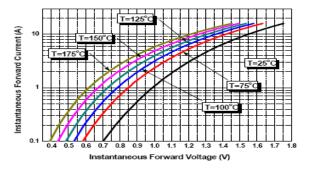


Figure 1. Typical Forward voltage V.S current

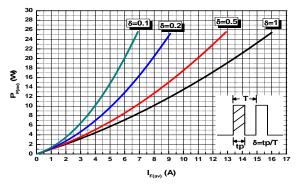


Figure 3. Average Forward Power Dissipation per Diode

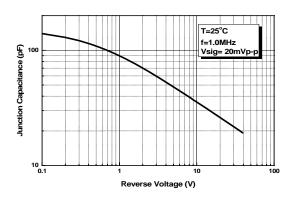


Figure 5. Typical Junction Capacitance

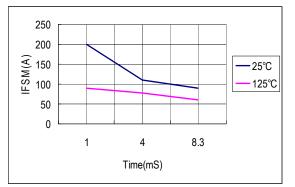


Figure 7. Peak forward surge current (single half sine wave)

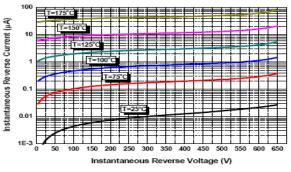


Figure 2. Typical Reverse Characteristics per Diode

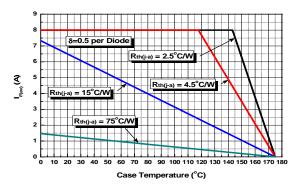


Figure 4. Current derating Curves

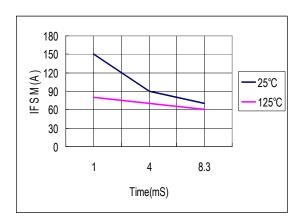
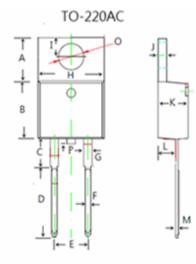


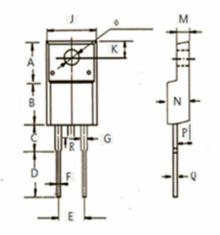
Figure 6. Peak forward surge current (square-wave)

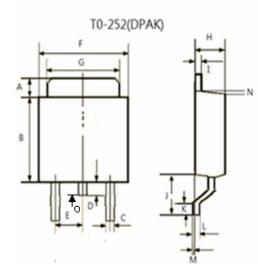


PACKAGE DIMENSION



TO-220FP





Dimension	Millimeters		Dimension	Millin	meters
	Min.	Max.	DIMENSION	Min.	Max.
A	б.17	7.00	Н	9.80	10.50
В	8.50	9.45	Ι	2.59	2.95
С	2.56	4.43	J	1.14	1.40
D	8.98	10.80	К	4.20	4.80
E	4.60	5.60	L	2.20	2.82
F	0.70	0.91	М	0.28	0.60
G	1.17	1.55	0	3.56	3.94
			Р		1.00

Dimension	Millimeters		Dimension	Millin	neters
	Min.	Max.	DIMENSION	Min.	Max.
А	5.84	6.98	J	9.90	10.50
В	8.05	9.97	К	2.50	3.80
С	2.79	4.10	М	2.34	3.30
D	8.94	10.65	N	4.20	4.90
E	4.60	5.60	0	2.08	3.56
F	0.30	0.90	Р	2.45	2.92
G	1.08	1.48	Q	0.35	0.80
			R		1.00

Dimension	Millimeters		Dimension	Millin	neters
	Min.	Max.	Dimension	Min.	Max.
А	0.89	1.65	Н	2.19	2.40
В	5.95	б.25	Ι	0.43	0.58
С	0.50	0.86	J	2.43	2.90
D	0.60	1.02	К	1.25	1.78
E	2.18	2.39	L	0.43	0.60
F	6.35	6.75	М	0.00	10°
G	5.10	5.46	Ν	0.00	15°
			0		1.55

2014/09/30 Rev1.8



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